Icemos Technology Ltd **Product Specification** **1000.771901** Issue Date 25 March 2025 07:4

Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none or semi standard	
	5.0	Overall Thickness	488.00 +/- 8.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<10.00µm	Guaranteed by Process
	7.0	Bow	<120.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<120.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	400.00 +/- 5.00 µm	ADE, 100%
	14.0	Handle Doping Type	p	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.01-0.02 Ohm-cm	Wafer Vendor
	17.0	Backside Finish	Polished with lasermarking, light handling marks, and Oxide.	Guaranteed by Process
BuriedOxide	18.0	Oxide Type	Thermal	
	19.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	20.0	Oxide formed on	Handle Wafer	
DeviceSilicon	21.0	Device Growth Method	CZ	Wafer Vendor
	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	50.00 +/- 1.00 µm	ADE, 100%
	24.0	Device Doping Type	P	Wafer Vendor
	25.0	Device Dopant	Boron	Wafer Vendor
	26.0	Device Resistivity	0.01-0.02 Ohm-cm	Wafer Vendor
BuriedOxide2	27.0	Oxide 2 Type	Thermal	
	28.0	Oxide 2 Thickness	10,000.00 +/- 1,000.00 A	Nanospec centre point measurement, 4%
	29.0	Oxide 2 formed on	Device wafer (Any)	Guaranteed by Process
DeviceSilicon2	30.0	Device 2 Growth Method	CZ	Wafer Vendor
	31.0	Device 2 Orientation	{100} +/- 0.5 degree	Wafer Vendor
	32.0	Device 2 Nominal Thickness	35.00 +/- 1.00 um	ADE, 100%
	33.0	Device 2 DopingType	P	Wafer Vendor
	34.0	Device 2 Dopant	Boron	Wafer Vendor
	35.0	Device 2 Resistivity	0.01-0.02 Ohm-cm	Wafer Vendor

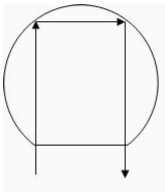
Part Number	Customer

Category		**Parameter**	**Specification**	**Measurement Method**
DeviceSilicon2	36.0	Device 2 Field Oxidation	10,000.00 +/- 1,000.00 A	Nanospec centre point measurement, 4%
DeviceSilicon	37.0	Voids	none	Bright Light, 100% (note 2)
	38.0	Scratches	0	Bright Light, 100% (note 2)
	39.0	Haze	none	Bright Light, 100% (note 2)

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

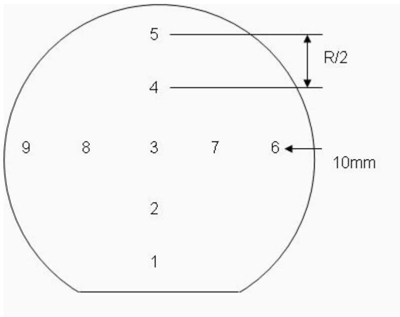
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information